

Artificially nanostructured n-type SiGe bulk thermoelectrics through plasma enhanced growth of alloy nanoparticles from the gas phase – CORRIGENDUM

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In the last sentence of the abstract, “1000 °C” is incorrect:

“A figure of merit of $zT = 0.5 \pm 0.09$ at 450 °C and a peak zT of 0.8 ± 0.15 at 1000 °C could be achieved for a nanostructured, 0.8% phosphorus-doped $\text{Si}_{80}\text{Ge}_{20}$ alloy without any further optimization.”

The correct temperature is 800 °C.

REFERENCE

N. Stein, N. Petermann, R. Theissmann, G. Schierning, R. Schmechel, and H. Wiggers: Artificially nanostructured n-type SiGe bulk thermoelectrics through plasma enhanced growth of alloy nanoparticles from the gas phase. *J. Mater. Res.* **26**(15), 1872 (2011).